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PATENT

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FEE PAID

October 22, 2003
Date

Ayesha S. Wilks

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Appl. No. : 10/054,692

Confirmation No. : 8574

Applicants : Trung T. Doan and Gurtej S. Sandhu

Filed : December 19, 2001

Attorney Docket No.: 500300.02

Art Unit : 3725

Customer No. : 27,076

Examiner : William Hong

Title : POLISHING PAD REFURBISHER FOR IN SITU, REAL-TIME CONDITIONING
AND CLEANING OF A POLISHING PAD USED IN CHEMICAL-MECHANICAL
POLISHING OF MICROELECTRONIC SUBSTRATES

Mail Stop Non-Fee Amendment
Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

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AMENDMENT

Sir:

Please amend the above-captioned patent application as follows:

In the Specification:

Please amend the paragraph of Patent No. 6,004,196 beginning on column 2, line 18, as follows:

CMP processes must also consistently and accurately produce a uniform, planar surface on the wafer because it is important to accurately focus the image of circuit patterns on the surface of the wafer. As the density of integrated circuits increases, it is often necessary to accurately focus the critical dimensions of the circuit pattern to better than a tolerance of

approximately $0.1 \mu\text{m}$. Focusing the circuit patterns to such small tolerances, however, is very difficult when the distance between the emission source and the surface of the wafer varies because the surface of the wafer is not uniformly planar. In fact, several devices may be defective on a wafer with a non-[uniformly] uniformly planar surface. Thus, CMP processes must create a highly uniform, planar surface.
